General Description

The AAT7551 is a dual low threshold P-channel MOSFET designed for the battery, cell phone, and PDA markets. Using AnalogicTech's ultra-high-density MOSFET process and space-saving, small outline, J-lead package, performance superior to that normally found in a TSOP-6 footprint has been squeezed into the footprint of an SC70JW-8 package.

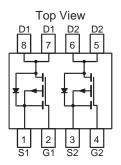
Applications

- Battery Packs
- Battery-Powered Portable Equipment
- Cellular and Cordless Telephones

Features

- Drain-Source Voltage (max): -20V
- Continuous Drain Current¹ (max):
 -2.7A @ 25°C
- Low On-Resistance:
 - 100mΩ @ V_{GS} = -4.5V
 - 175mΩ @ V_{GS} = -2.5V

Dual SC70JW-8 Package



Absolute Maximum Ratings

 $T_A = 25$ °C, unless otherwise noted.

Symbol	Description	Value	Units		
V _{DS}	Drain-Source Voltage		-20	V	
V_{GS}	Gate-Source Voltage		±12	v	
I _D	Continuous Drain Current @ T _J = 150°C¹	$T_A = 25$ °C	±2.7		
		$T_A = 70$ °C	±2.2	Α	
I _{DM}	Pulsed Drain Current ²		±8	^	
Is	Continuous Source Current (Source-Drain Diode) ¹	-0.6			
T _J	Operating Junction Temperature Range	-55 to 150	°C		
T _{STG}	Storage Temperature Range	-55 to 150	°C		

Thermal Characteristics¹

Symbol	Description		Тур	Max	Units	
$R_{\theta JA}$	Junction-to-Ambient Steady State		132	165	°C/W	
$R_{\theta JA2}$	Junction-to-Ambient t<5 Seconds		83	104		
$R_{\theta JF}$	Junction-to-Foot		60	72		
P _D	Maximum Power Dissipation	T _A = 25°C		1.2	W	
		T _A = 70°C		0.75	VV	

^{1.} Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications. $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$ where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. $R_{\theta JF}$ is guaranteed by design; however, $R_{\theta CA}$ is determined by the PCB design. Actual maximum continuous current is limited by the application's design.

7551.2005.04.1.0

^{2.} Pulse test: Pulse Width = 300µs.



Electrical Characteristics

 $T_J = 25$ °C, unless otherwise noted.

Symbol	Description	Conditions	Min	Тур	Max	Units	
DC Chara	DC Characteristics						
BV _{DSS}	Drain-Source Breakdown	$V_{GS} = 0V, I_{D} = -250\mu A$	-20			V	
	Voltage						
R _{DS(ON)}	Drain-Source On-Resistance ¹	$V_{GS} = -4.5V, I_D = -2.7A$		80	100	mΩ	
		$V_{GS} = -2.5V, I_D = -2.0A$		140	175	11122	
I _{D(ON)}	On-State Drain Current ¹	$V_{GS} = -4.5V$, $V_{DS} = -5V$ (pulsed)	-8			Α	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = -250\mu A$	-0.6			V	
I _{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 12V$, $V_{DS} = 0V$			±100	nA	
	Drain Source Leakage Current	$V_{GS} = 0V$, $V_{DS} = -20V$			-1	μA	
I _{DSS}		$V_{GS} = 0V, V_{DS} = -16V, T_{J} = 70^{\circ}C^{2}$	-5		μΑ		
g_{fs}	Forward Transconductance ¹	$V_{DS} = -5V, I_{D} = -2.7A$		4		S	
Dynamic	Dynamic Characteristics ²						
Q_{G}	Total Gate Charge	$V_{DS} = -10V, R_D = 3.7\Omega, V_{GS} = -4.5V$		5.9			
Q_{GS}	Gate-Source Charge	$V_{DS} = -10V$, $R_D = 3.7\Omega$, $V_{GS} = -4.5V$		1		nC	
Q_GD	Gate-Drain Charge	$V_{DS} = -10V, R_D = 3.7\Omega, V_{GS} = -4.5V$		2			
t _{D(ON)}	Turn-On Delay	$V_{DS} = -10V$, $R_{D} = 3.7\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$		22			
t _R	Turn-On Rise Time	$V_{DS} = -10V$, $R_{D} = 3.7\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$		10		ns	
t _{D(OFF)}	Turn-Off Delay	$V_{DS} = -10V$, $R_{D} = 3.7\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$		20		115	
t _F	Turn-Off Fall Time	$V_{DS} = -10V$, $R_{D} = 3.7\Omega$, $V_{GS} = -4.5V$, $R_{G} = 6\Omega$		40			
Source-Drain Diode Characteristics							
V _{SD}	Source-Drain Forward	$V_{GS} = 0, I_{S} = -2.7A$			-1.3	V	
	Voltage ¹						
I _S	Continuous Diode Current ³				-0.6	Α	

2 7551.2005.04.1.0

^{1.} Pulse test: Pulse Width = 300µs.

^{2.} Guaranteed by design. Not subject to production testing.

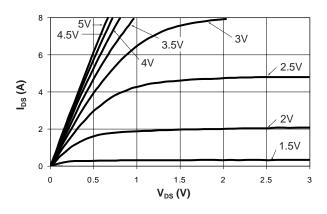
^{3.} Based on thermal dissipation from junction to ambient while mounted on a 1" x 1" PCB with optimized layout. A 5-second pulse on a 1" x 1" PCB approximates testing a device mounted on a large multi-layer PCB as in most applications. $R_{\theta JF} + R_{\theta FA} = R_{\theta JA}$ where the foot thermal reference is defined as the normal solder mounting surface of the device's leads. $R_{\theta JF}$ is guaranteed by design; however, $R_{\theta CA}$ is determined by the PCB design. Actual maximum continuous current is limited by the application's design.



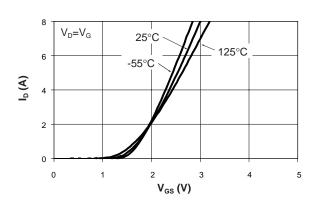
Typical Characteristics

 $T_{.1} = 25^{\circ}$ C, unless otherwise noted.

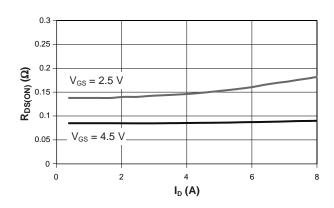
Output Characteristics



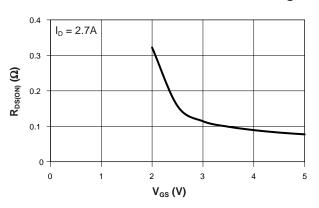
Transfer Characteristics



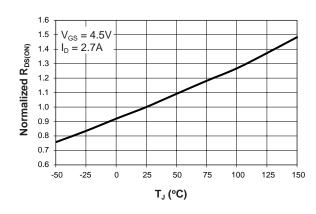
On-Resistance vs. Drain Current



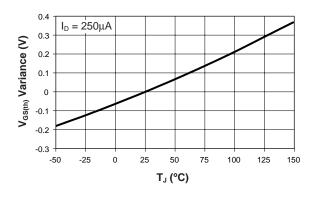
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Threshold Voltage



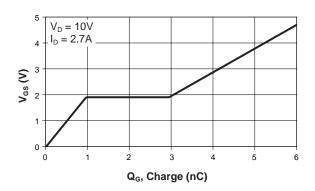
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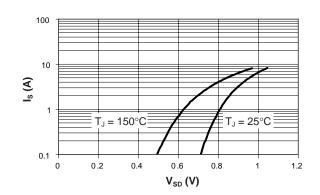
Typical Characteristics

 $T_J = 25^{\circ}$ C, unless otherwise noted.

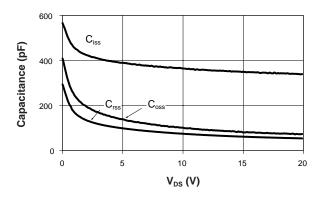
Gate Charge



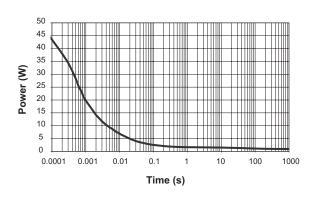
Source-Drain Diode Forward Voltage



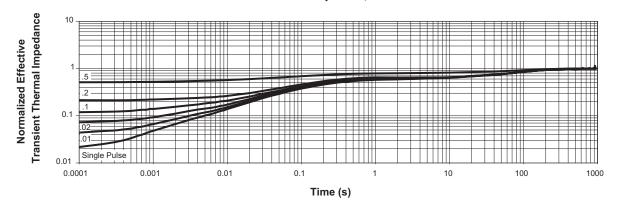
Capacitance



Single Pulse Power, Junction to Ambient



Transient Thermal Response, Junction to Ambient



4 7551.2005.04.1.0

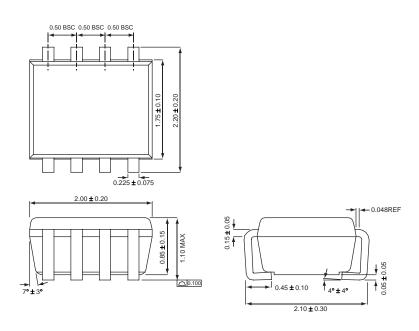


Ordering Information

Package	Marking ¹	Part Number (Tape and Reel) ²
SC70JW-8	KDXYY	AAT7551IJS-T1

Package Information

SC70JW-8



All dimensions in millimeters.

7551.2005.04.1.0

^{1.} XYY = assembly and date code.

^{2.} Sample stock is generally held on part numbers listed in BOLD.



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6 *7551.2005.04.1.0*